



PATENT

ATTY. DKT. AMAT/8539/TSG/EPI/RKK

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

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Kim et al.

§

Serial No.: 10/683,937

§

Group Art Unit: 2812

§

Confirmation No.: 2191

§

§

Filed: October 10, 2003

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Examiner: Unassigned

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For: Method of Selective Deposition of
Heavily Doped Epitaxial SiGe

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Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATE OF MAILING

37 CFR 1.8

I hereby certify that this correspondence is being deposited on January 21, 2005 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

January 21, 2005

Date

Signature

Dear Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this **Supplemental** Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

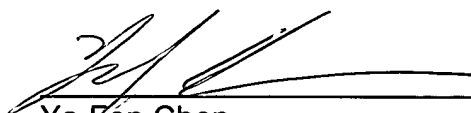
In accordance with 37 CFR § 1.97, this **Supplemental** Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

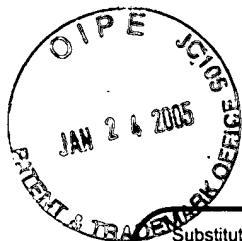
Applicants certify that all references submitted with this disclosure were first cited in a communication from a foreign patent office dated January 4, 2005, which communication is enclosed, not more than three months prior to the filing of this **Supplemental** Information Disclosure Statement.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/8539/BTP.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Ya-Fen Chen', is written over a horizontal line.

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**SUPPLEMENTAL
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known

Application Number	10/683,937
Filing Date	October 10, 2003
First Named Inventor	Kim et al.
Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	AMAT/8539/TSG/EPI/RKK

NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	C1	Article by Uchino et al., entitled "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-µm CMOS ULSIs", IEDM, December 1997, Technical Digest, pgs. 479-482.	
	C2	Article by Sedgwick et al., entitled "Selective SiGe and heavily as doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science & Technology, May/June 1993, No. 3, pgs. 1124-1128.	
	C3	Article by Kamins et al., entitled "Kinetics of Selective epitaxial deposition Si _{1-x} Ge _x ", American Institute of Physics, 1992/August, No. 6, pgs. 669-671	
	C4	Article by Menon et al., entitled "Loading effect in SiGe layers grown by dichlorosilane- and silane-based epitaxy", American Institute of Physics, 2001/November, Volume 90. No. 9, pgs. 4805-4809.	
	C5		
	C6		
	C7		
	C8		
	C9		
	C10		
	C11		
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

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